

# 2–8 GHz Medium Power Gallium Arsenide FET

## Technical Data

**ATF-45101**

### Features

- **High Output Power:**  
29.0 dBm Typical  $P_{1\text{dB}}$  at 4 GHz
- **High Gain at 1dB Compression:**  
10.0 dB Typical  $G_{1\text{dB}}$  at 4 GHz
- **High Power Efficiency:**  
38% Typical at 4 GHz
- **Hermetic Metal-Ceramic Stripline Package**

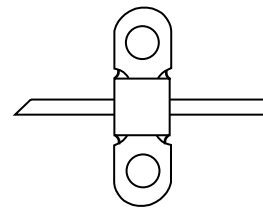
### Description

The ATF-45101 is a gallium arsenide Schottky-barrier-gate field effect transistor designed for medium power, linear amplification in the 2 to 8 GHz frequency

range. This nominally 0.5 micron gate length GaAs FET is an interdigitated four-cell structure using airbridge interconnects between drain fingers. Total gate periphery is 2.5 millimeters. Proven gold based metallization systems and nitride passivation assure a rugged, reliable device.

This device is suitable for applications in space, airborne, military ground and shipboard, and commercial environments. It is supplied in a hermetic high reliability package with low parasitic reactance and minimum thermal resistance.

### 100 mil Flange Package



### Electrical Specifications, $T_A = 25^\circ\text{C}$

Symbol	Parameters and Test Conditions	Units	Min.	Typ.	Max.	
$P_{1\text{dB}}$	Power Output @ 1 dB Gain Compression: $V_{\text{DS}} = 9\text{ V}, I_{\text{DS}} = 250\text{ mA}$	$f = 4.0\text{ GHz}$ $f = 8.0\text{ GHz}$	dBm	28.0	29.0 28.0	
$G_{1\text{dB}}$	1 dB Compressed Gain: $V_{\text{DS}} = 9\text{ V}, I_{\text{DS}} = 250\text{ mA}$	$f = 4.0\text{ GHz}$ $f = 8.0\text{ GHz}$	dB	9.0	10.0 4.0	
$\eta_{\text{add}}$	Efficiency @ $P_{1\text{dB}}$ : $V_{\text{DS}} = 9\text{ V}, I_{\text{DS}} = 250\text{ mA}$	$f = 4.0\text{ GHz}$	%		38	
$g_m$	Transconductance: $V_{\text{DS}} = 2.5\text{ V}, I_{\text{DS}} = 250\text{ mA}$		mmho		200	
$I_{\text{DSS}}$	Saturated Drain Current: $V_{\text{DS}} = 1.75\text{ V}, V_{\text{GS}} = 0\text{ V}$		mA	400	600	800
$V_P$	Pinch-off Voltage: $V_{\text{DS}} = 2.5\text{ V}, I_{\text{DS}} = 12.5\text{ mA}$		V	-5.4	-4.0	-2.0

## ATF-45101 Absolute Maximum Ratings

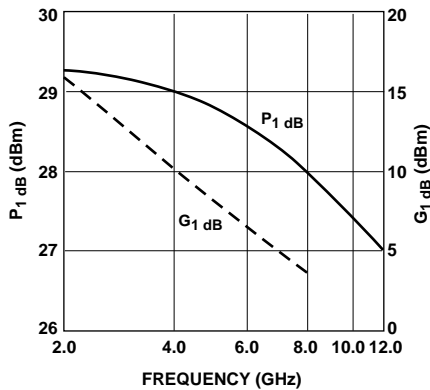
Symbol	Parameter	Units	Absolute Maximum <sup>[1]</sup>
$V_{DS}$	Drain-Source Voltage	V	+14
$V_{GS}$	Gate-Source Voltage	V	-7
$V_{GD}$	Gate-Drain Voltage	V	-16
$I_{DS}$	Drain Current	mA	$I_{DSS}$
$P_T$	Power Dissipation <sup>[2,3]</sup>	W	3.6
$T_{CH}$	Channel Temperature	°C	175
$T_{STG}$	Storage Temperature	°C	-65 to +175

**Thermal Resistance:**  $\theta_{jc} = 42^\circ\text{C/W}; T_{CH} = 150^\circ\text{C}$   
**Liquid Crystal Measurement:** 1  $\mu\text{m}$  Spot Size<sup>[4]</sup>

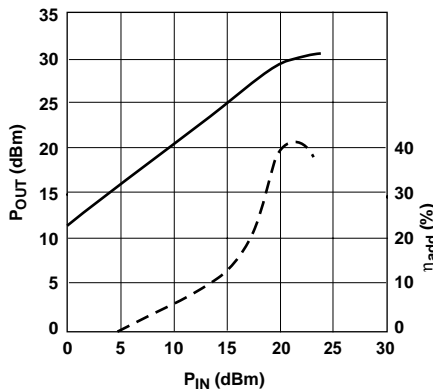
### Notes:

1. Permanent damage may occur if any of these limits are exceeded.
2.  $T_{CASE\ TEMPERATURE} = 25^\circ\text{C}$ .
3. Derate at  $24\ \text{mW}/^\circ\text{C}$  for  $T_{CASE} > 24^\circ\text{C}$ .
4. The small spot size of this technique results in a higher, though more accurate determination of  $\theta_{jc}$  than do alternate methods. See MEASUREMENTS section for more information.

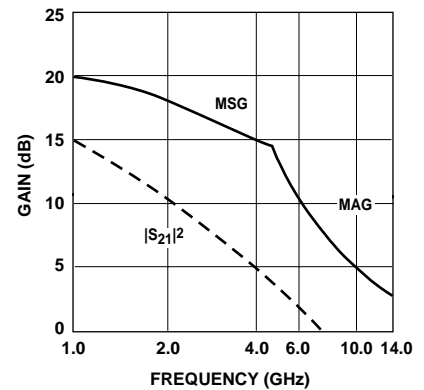
## ATF-45101 Typical Performance, $T_A = 25^\circ\text{C}$



**Figure 1. Power Output @ 1 dB Gain Compression and 1 dB Compressed Gain vs. Frequency.**  
 $V_{DS} = 9\text{V}, I_{DS} = 250\text{mA}$ .



**Figure 2. Output Power and Power Added Efficiency vs. Input Power.**  
 $V_{DS} = 9\text{V}, I_{DS} = 250\text{mA}, f = 4.0\text{GHz}$ .



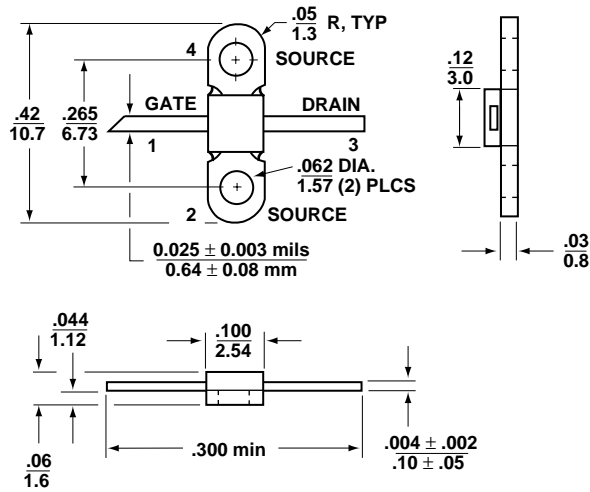
**Figure 3. Insertion Power Gain, Maximum Available Gain and Maximum Stable Gain vs. Frequency.**  
 $V_{DS} = 9\text{V}, I_{DS} = 250\text{mA}$ .

**Typical Scattering Parameters, Common Emitter,  $Z_0 = 50 \Omega$ ,  $T_A = 25^\circ\text{C}$ ,  $V_{DS} = 9\text{V}$ ,  $I_{DS} = 250\text{mA}$**

Freq. GHz	$S_{11}$		dB	$S_{21}$		dB	$S_{12}$		$S_{22}$	
	Mag.	Ang.		Mag.	Ang.		Mag.	Ang.	Mag.	Ang.
1.0	.89	-88	14.9	5.54	119	-26.2	.049	43	.31	-63
2.0	.83	-135	10.8	3.48	82	-26.0	.050	18	.33	-108
3.0	.81	-158	7.6	2.40	58	-25.8	.051	7	.39	-129
4.0	.84	-174	5.4	1.86	38	-25.5	.053	3	.46	-144
5.0	.82	-170	3.8	1.55	18	-25.2	.055	-2	.50	-154
6.0	.81	152	2.6	1.36	-2	-24.4	.060	-8	.52	-168
7.0	.81	133	1.2	1.15	-25	-23.9	.064	-15	.55	173
8.0	.81	122	-0.3	.97	-42	-23.5	.067	-20	.59	154
9.0	.80	113	-1.8	.81	-60	-22.6	.074	-31	.64	137
10.0	.79	107	-3.2	.69	-73	-22.0	.079	-40	.68	123
11.0	.77	94	-4.6	.59	-91	-21.5	.084	-45	.72	113
12.0	.73	82	-5.8	.51	-106	-20.3	.097	-55	.76	99
13.0	.68	69	-6.7	.46	-123	-18.3	.121	-63	.78	89
14.0	.64	56	-7.1	.44	-137	-15.9	.161	-79	.80	79

A model for this device is available in the DEVICE MODELS section.

**100 mil Flange Package Dimensions**



- Notes:**  
 (unless otherwise specified)  
 1. Dimensions are in mm  
 2. Tolerances  
 in .xxx = ± 0.005  
 mm .xx = ± 0.13

Package marking code is 451